Vincotech

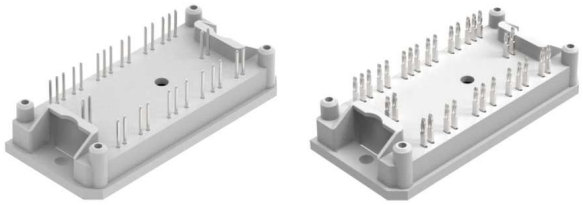
10-F1126PA050M7-L828F09
10-P1126PA050M7-L828F09Y
datasheet

***flow* PACK 1** **1200 V / 50 A**

Features

- IGBT M7 technology with low V_{CEsat} and improved EMC behavior
- Compact and low inductive design
- Built-in NTC

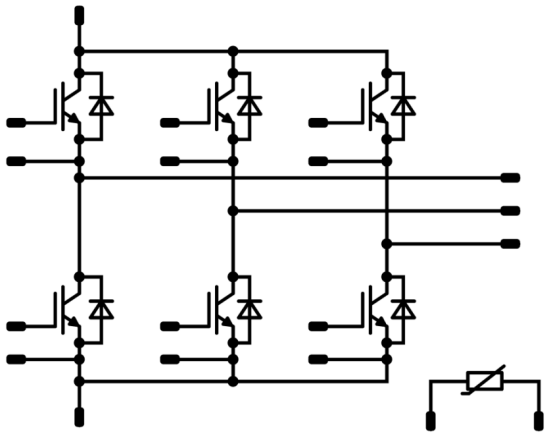
flow 1 17 mm housing



Target applications

- Industrial Drives
- UPS

Schematic



Types

- 10-F1126PA050M7-L828F09
- 10-P1126PA050M7-L828F09Y

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C		50	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	100	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	115	W
Gate-emitter voltage	V_{GES}		±20	V
Maximum junction temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Inverter Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F		50	A
Repetitive peak forward current	I_{FRM}	t_j limited by T_{jmax}	100	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	104	W
Maximum junction temperature	T_{jmax}		175	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
		AC Voltage t_p = 1 min	2500	V
Creepage distance			min. 12,7	mm
Clearance		Solder pin / Press-fit pin	12,64 / min. 12,7	mm
Comparative Tracking Index	CTI		> 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}$			0,005	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		50	25 125 150		1,55 1,77 1,83	1,9	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			90	µA
Gate-emitter leakage current	I_{GES}		15	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}	f = 10 MHz	0	10		25		10000		pF
Output capacitance	C_{oes}							350		
Reverse transfer capacitance	C_{res}							130		
Gate charge	Q_g		15	600	50	25		410		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,82		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{goff} = 8 Ω R_{gon} = 8 Ω	±15	600	48	25 125 150		176 176 190		ns
Rise time	t_r					25 125 150		52 58 60		
Turn-off delay time	$t_{d(off)}$					25 125 150		206 229 241		
Fall time	t_f					25 125 150		92 125 122		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 4,9 µC Q_{rFWD} = 7,1 µC Q_{rFWD} = 8 µC				25 125 150		4,82 6,38 6,25		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		2,98 4,25 5,03		

Characteristic Values

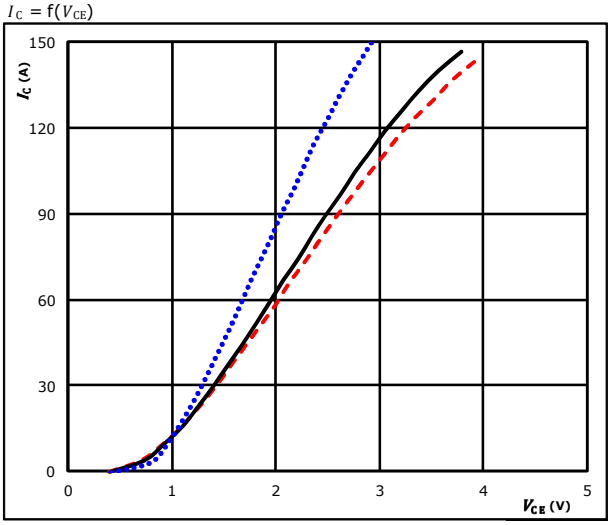
Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				50	25 125		1,66 1,78	2,15	V
Reverse leakage current	I_R			1200		25 150			50	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,91		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 338 A/µs di/dt = 450 A/µs di/dt = 498 A/µs	±15	600	48	25 125 150		29 33 33		A
Reverse recovery time	t_{rr}					25 125 150		339 435 511		ns
Recovered charge	Q_r					25 125 150		4,93 7,08 8,04		µC
Reverse recovered energy	E_{rec}					25 125 150		1,79 2,59 3,33		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		195 128 114		A/µs
Thermistor										
Rated resistance	R					25		4,7		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 401,3 Ω				100	-12,5		12,5	%
Power dissipation	P					25		5		mW
Power dissipation constant						25		1,3		mW/K
B-value	$B_{(25/50)}$	Tol. ±3%				25		3612		K
B-value	$B_{(25/100)}$	Tol. ±3%				25		3650		K
Vincotech NTC Reference									U	

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

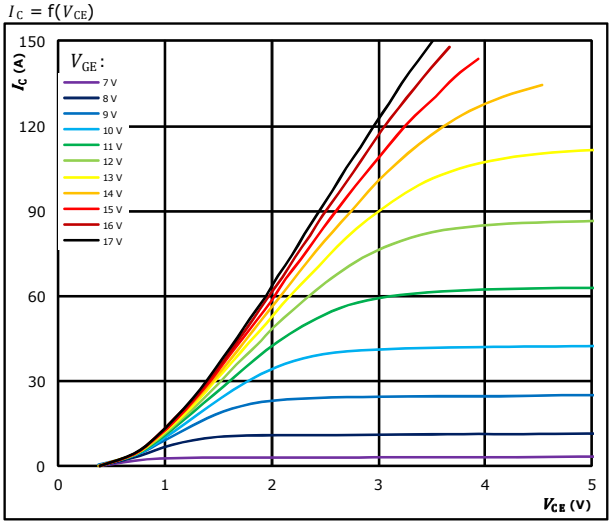


t_p =	250	µs		25 °C	
V_{GE} =	15	V	T_j:	125 °C	
				150 °C	

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

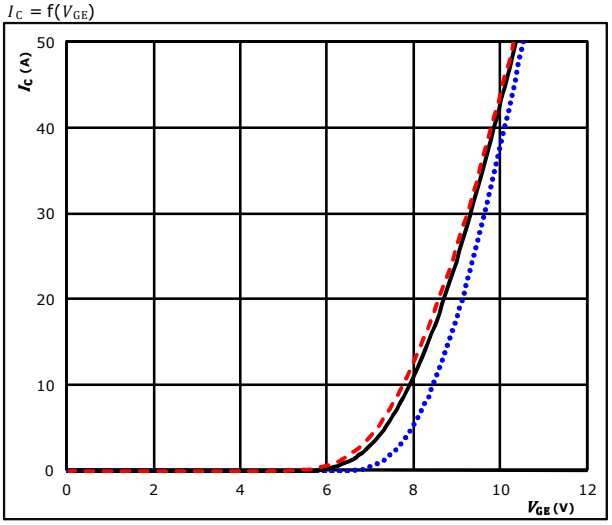


t_p =	250	µs
T_j =	150	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

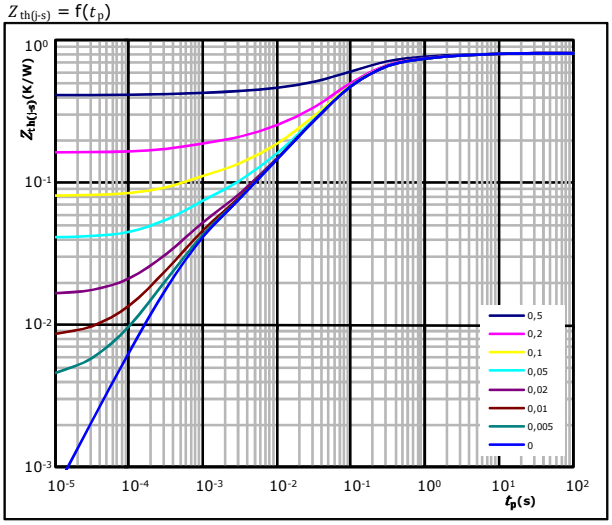


t_p =	100	µs		25 °C	
V_{CE} =	10	V	T_j:	125 °C	
				150 °C	

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	0,82	K/W

IGBT thermal model values

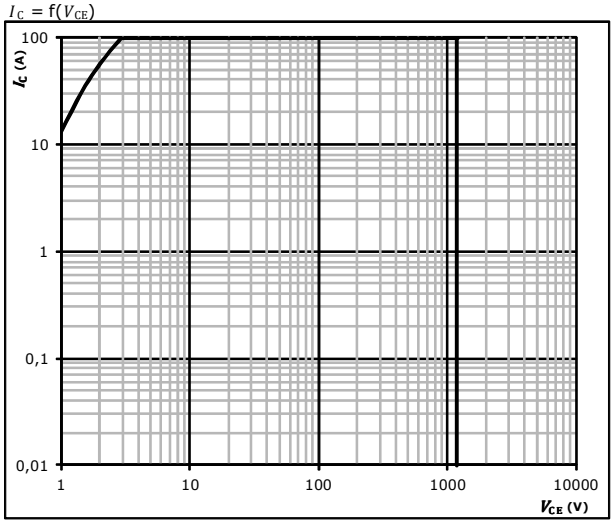
R (K/W)	τ (s)
4,05E-02	5,17E+00
8,54E-02	1,03E+00
3,18E-01	1,67E-01
2,80E-01	5,49E-02
6,47E-02	7,32E-03
3,43E-02	6,46E-04

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



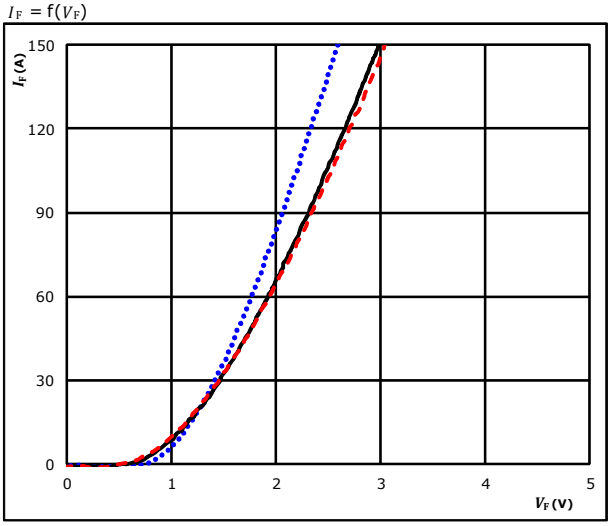
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Inverter Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



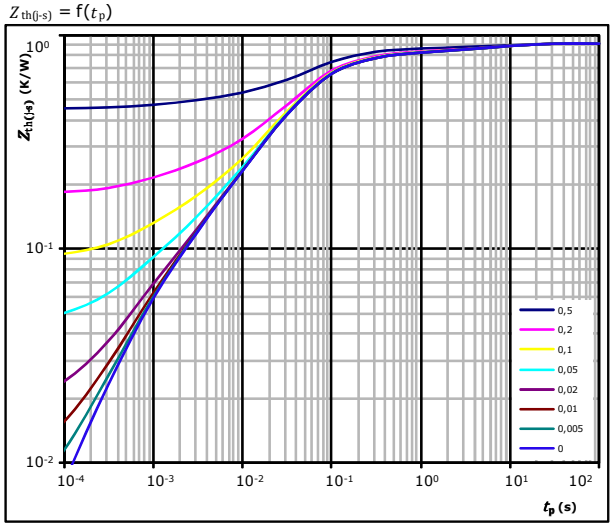
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 0,91 K/W

FWD thermal model values

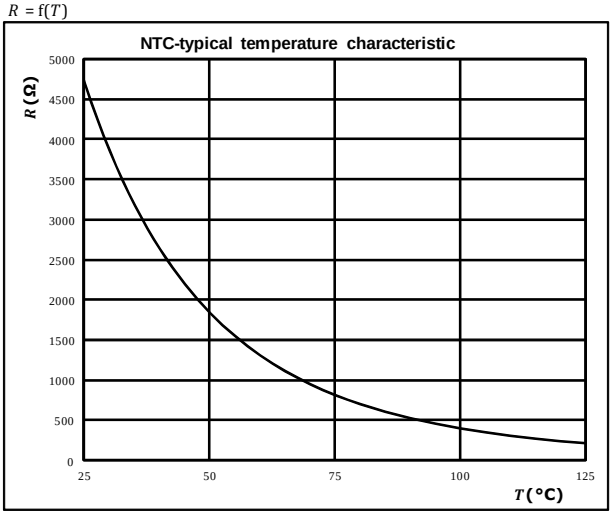
R (K/W)	τ (s)
8,48E-02	5,83E+00
9,67E-02	3,26E-01
4,29E-01	4,85E-02
1,97E-01	1,77E-02
6,32E-02	2,88E-03
3,90E-02	5,73E-04

Thermistor Characteristics

figure 1. **Thermistor**

Typical NTC characteristic

$R = f(T)$

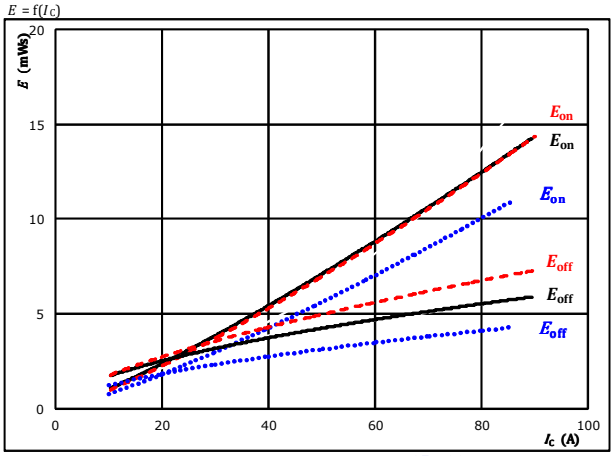


Inverter Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



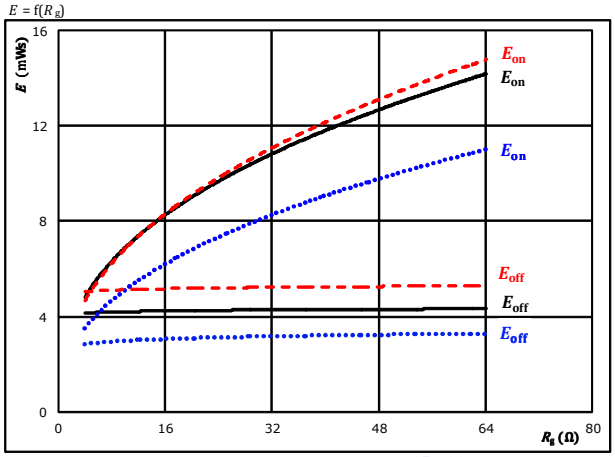
With an inductive load at

V_{CE} =	600	V	T_J:	25 °C	
V_{GE} =	±15	V		125 °C	
R_{gon} =	8	Ω		150 °C	
R_{goff} =	8	Ω			

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



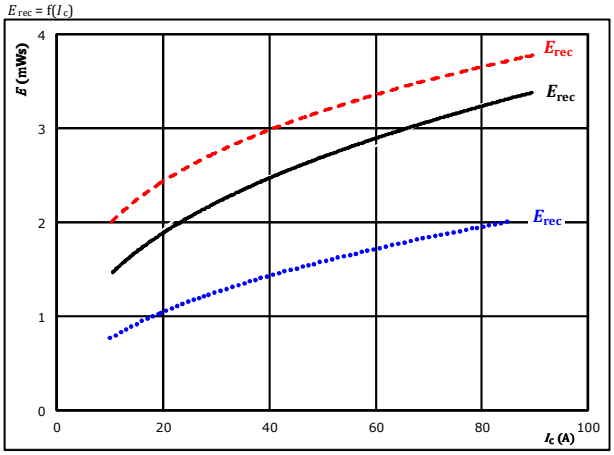
With an inductive load at

V_{CE} =	600	V	T_J:	25 °C	
V_{GE} =	±15	V		125 °C	
I_C =	48	A		150 °C	

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



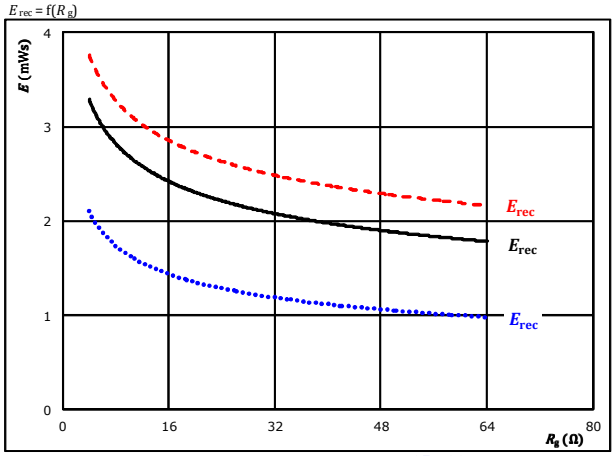
With an inductive load at

V_{CE} =	600	V	T_J:	25 °C	
V_{GE} =	±15	V		125 °C	
R_{gon} =	8	Ω		150 °C	

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

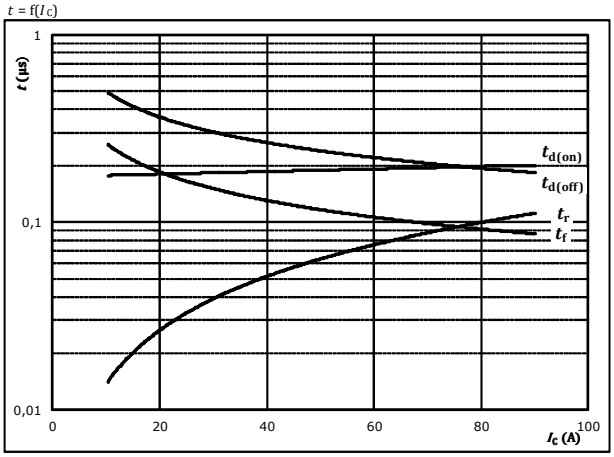
V_{CE} =	600	V	T_J:	25 °C	
V_{GE} =	±15	V		125 °C	
I_C =	48	A		150 °C	

Inverter Switching Characteristics

figure 5. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



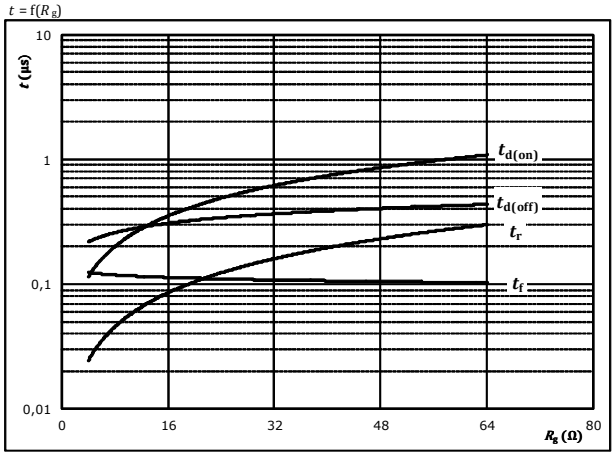
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 6. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_g)$



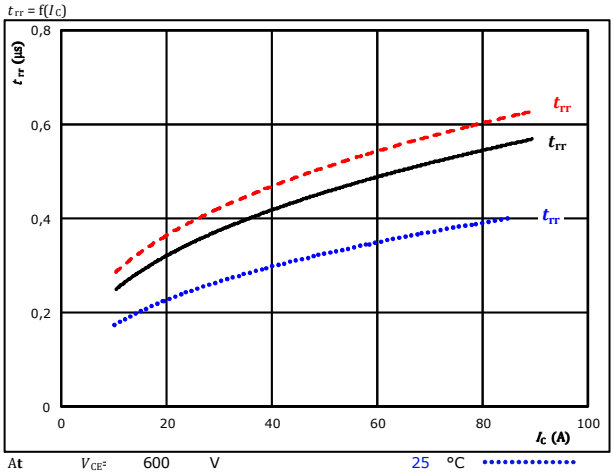
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	48	A

figure 7. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$

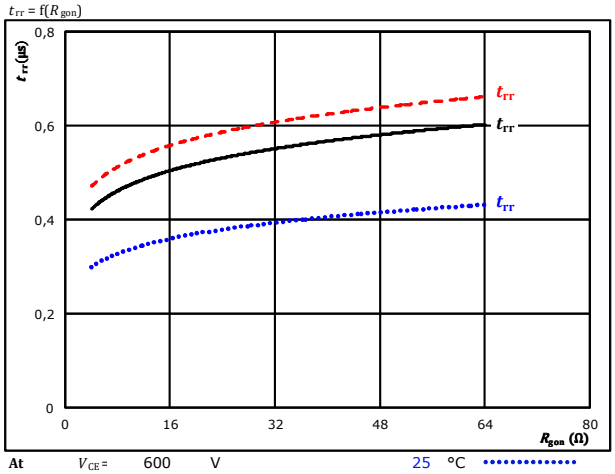


At					
	V_{CE} =	600	V		25 °C
	V_{GE} =	±15	V	T_j:	125 °C
	R_{gon} =	8	Ω		150 °C

figure 8. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



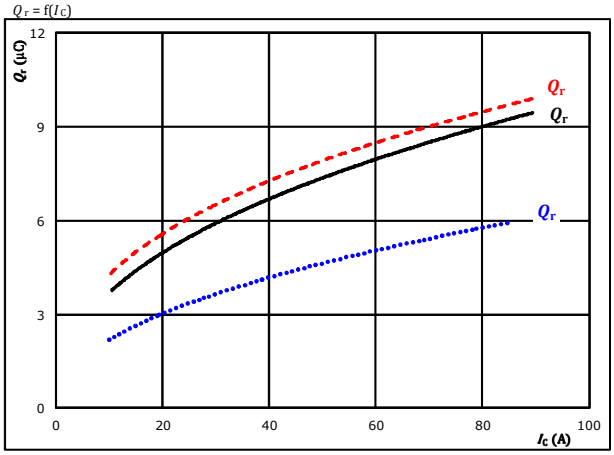
At					
	V_{CE} =	600	V		25 °C
	V_{GE} =	±15	V	T_j:	125 °C
	I_C =	48	A		150 °C

Inverter Switching Characteristics

figure 9. FWD

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

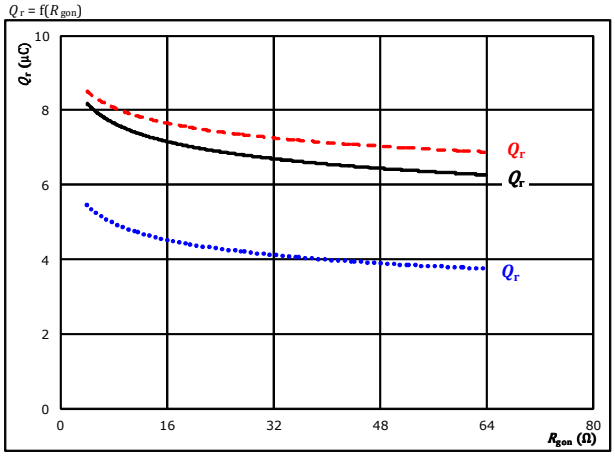


At						
V_{CE} =	600	V		25 °C	·····
V_{GE} =	±15	V	T_j:	125 °C	———
R_{gon} =	8	Ω		150 °C	– – –

figure 10. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

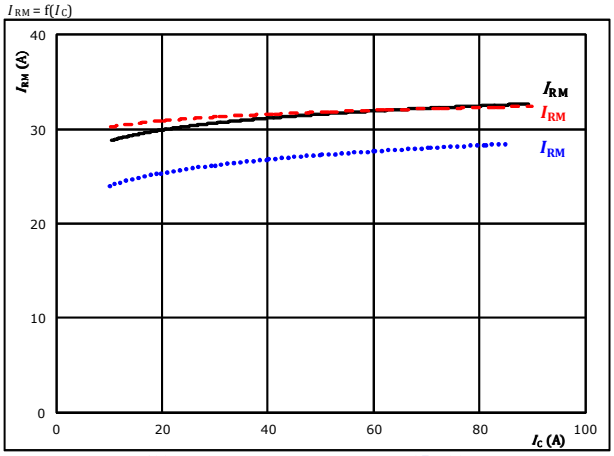


At						
V_{CE}=	600	V		25 °C	·····
V_{GE} =	±15	V	T_j:	125 °C	———
I_C=	48	A		150 °C	– – –

figure 11. FWD

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

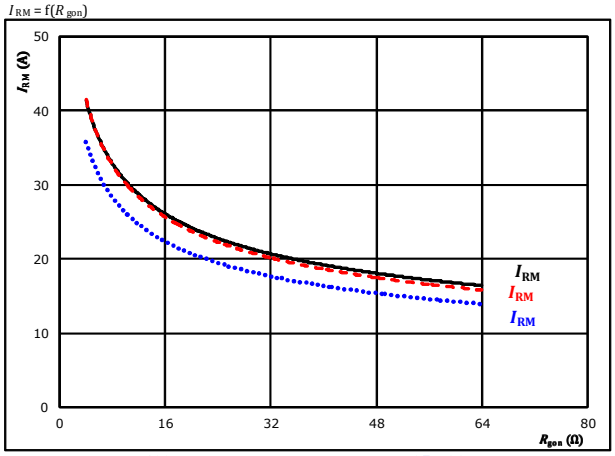


At						
V_{CE}:	600	V		25 °C	·····
V_{GE} =	±15	V	T_j:	125 °C	———
R_{gon} =	8	Ω		150 °C	– – –

figure 12. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



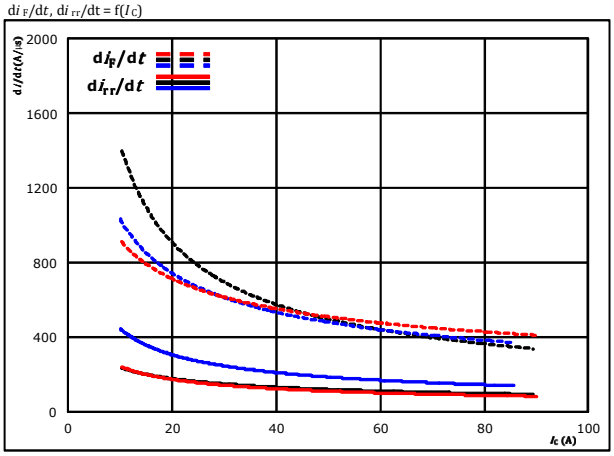
At						
V_{CE} =	600	V		25 °C	·····
V_{GE} =	±15	V	T_j:	125 °C	———
I_C =	48	A		150 °C	– – –

Inverter Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, $di_{rr}/dt = f(I_C)$

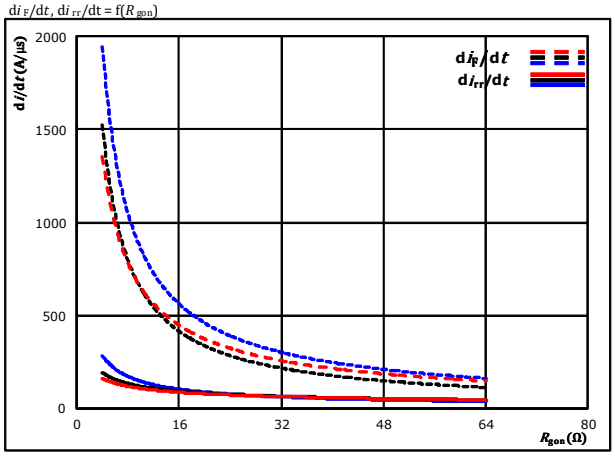


At						
V_{CE} =	600	V	T_j:	25 °C	•••••••••••••••
V_{GE} =	±15	V		125 °C	———
R_{gon} =	8	Ω		150 °C	– – – –

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

di_F/dt, $di_{rr}/dt = f(R_{gon})$

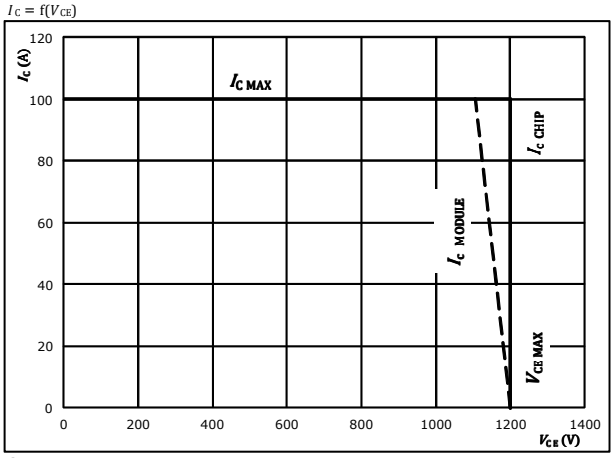


At						
V_{CE} =	600	V	T_j:	25 °C	•••••••••••••••
V_{GE} =	±15	V		125 °C	———
I_C =	48	A		150 °C	– – – –

figure 15. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j =	175	°C
R_{gon} =	8	Ω
R_{goff} =	8	Ω

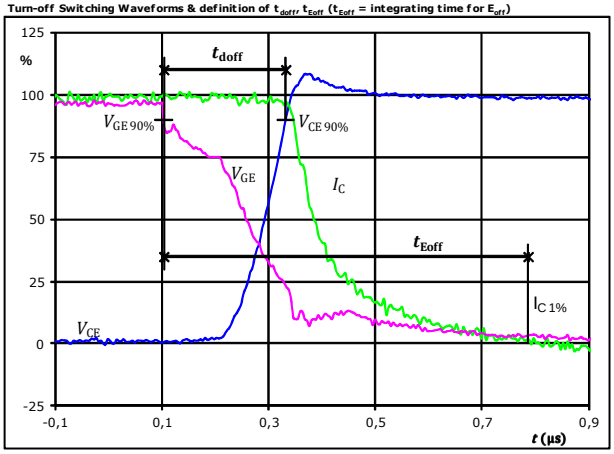
Inverter Switching Definitions

General conditions

T_j	=	**125 °C**
R_{gon}	=	**8 Ω**
R_{goff}	=	**8 Ω**

figure 1. IGBT

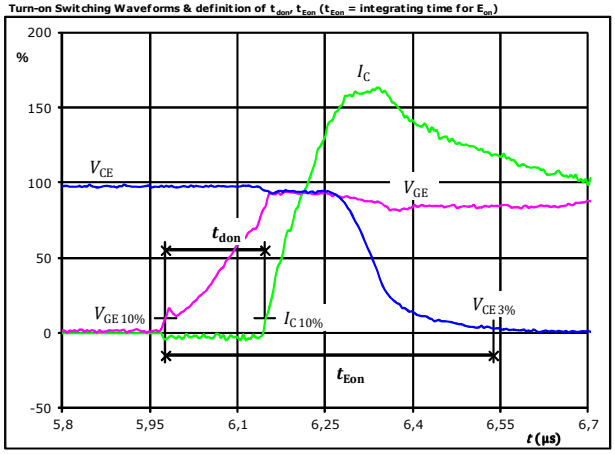
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	51	A
t_{doff} =	0,229	µs
t_{Eoff} =	0,683	µs

figure 2. IGBT

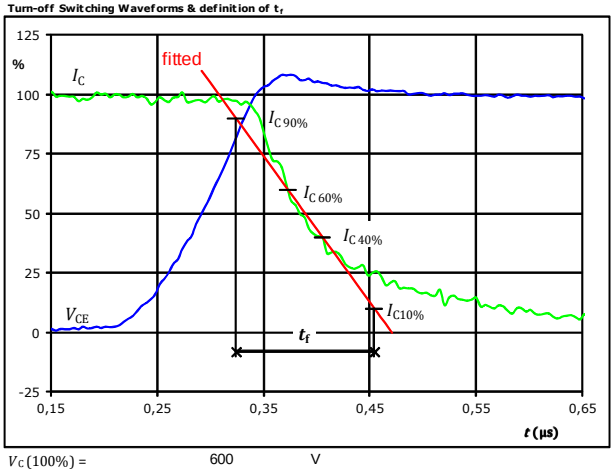
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	51	A
t_{don} =	0,176	µs
t_{Eon} =	0,561	µs

figure 3. IGBT

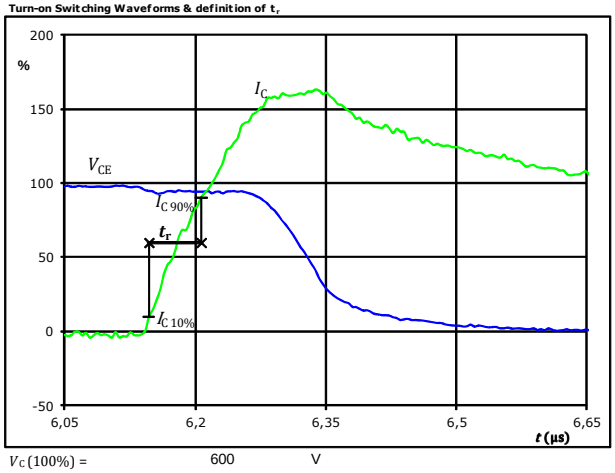
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	51	A
t_f =	0,125	µs

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

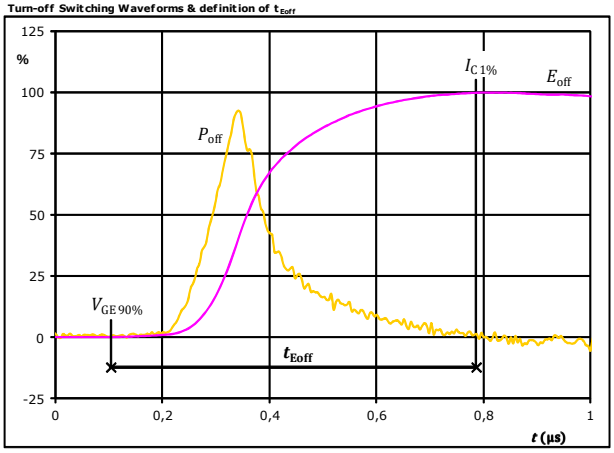


$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	51	A
t_r =	0,058	µs

Inverter Switching Characteristics

figure 5. **IGBT**

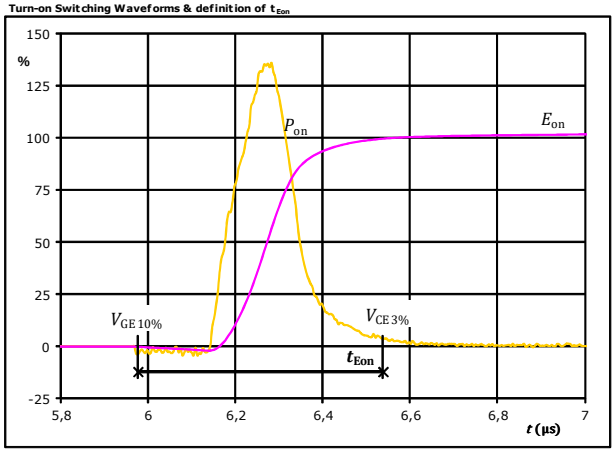
Turn-off Switching Waveforms & definition of t_{Eoff}



$P_{off}(100\%)$ =	30,49	kW
$E_{off}(100\%)$ =	4,25	mJ
t_{Eoff} =	0,68	µs

figure 6. **IGBT**

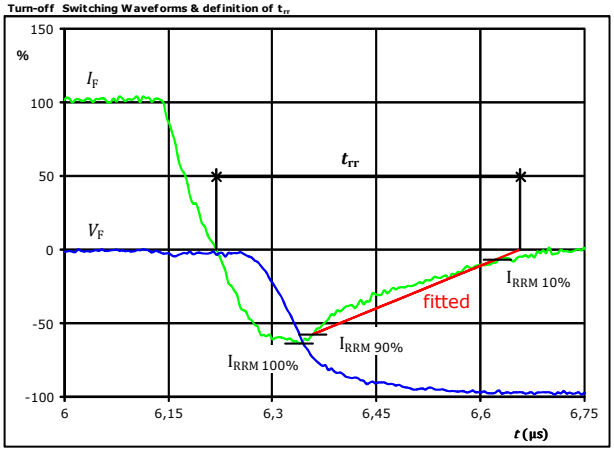
Turn-on Switching Waveforms & definition of t_{Eon}



$P_{on}(100\%)$ =	30,49	kW
$E_{on}(100\%)$ =	6,38	mJ
t_{Eon} =	0,56	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

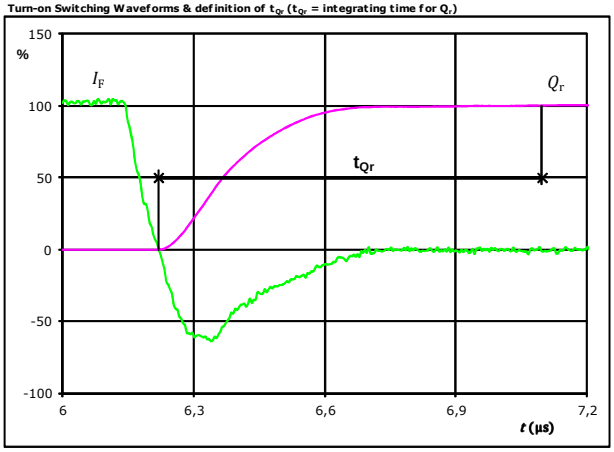


$V_F(100\%)$ =	600	V
$I_F(100\%)$ =	51	A
$I_{RRM}(100\%)$ =	-33	A
t_{rr} =	0,435	µs

Inverter Switching Characteristics

figure 8. **FWD**

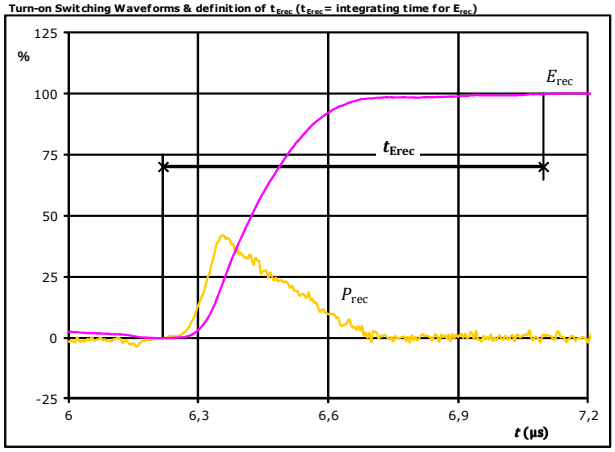
Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



I_F (100%) =	51	A
Q_r (100%) =	7,08	µC
t_{Qr} =	0,88	µs

figure 9. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



P_{rec} (100%) =	30,49	kW
E_{rec} (100%) =	2,59	mJ
t_{Erec} =	0,88	µs

Vincotech

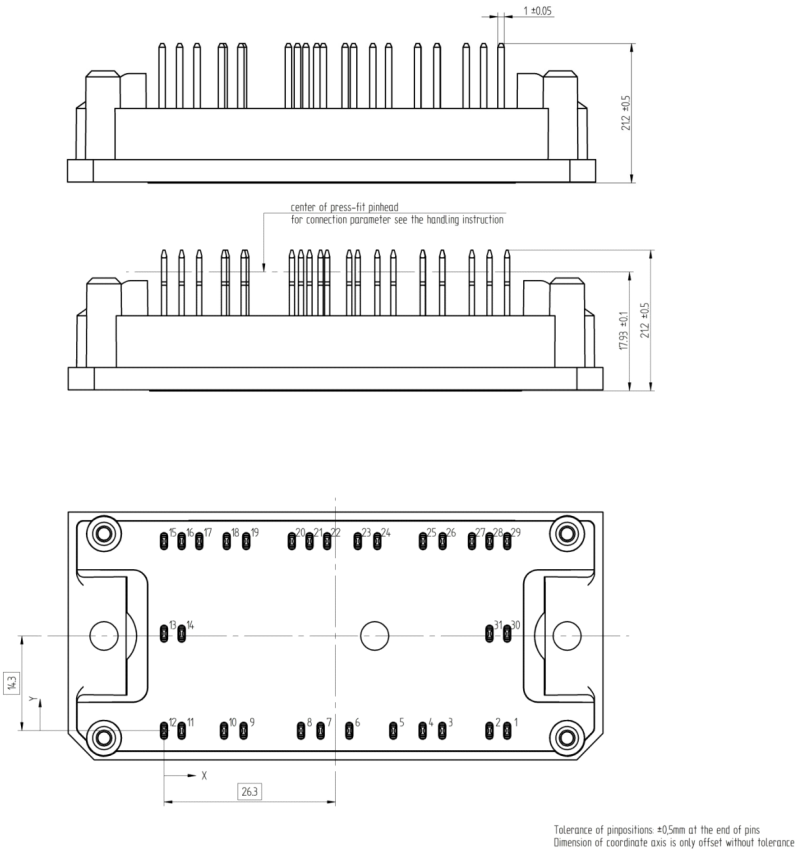
Ordering Code & Marking

Version	Ordering Code
without thermal paste 17 mm housing with solder pins	10-F1126PA050M7-L828F09
without thermal paste 17 mm housing with press-fit pins	10-P1126PA050M7-L828F09Y

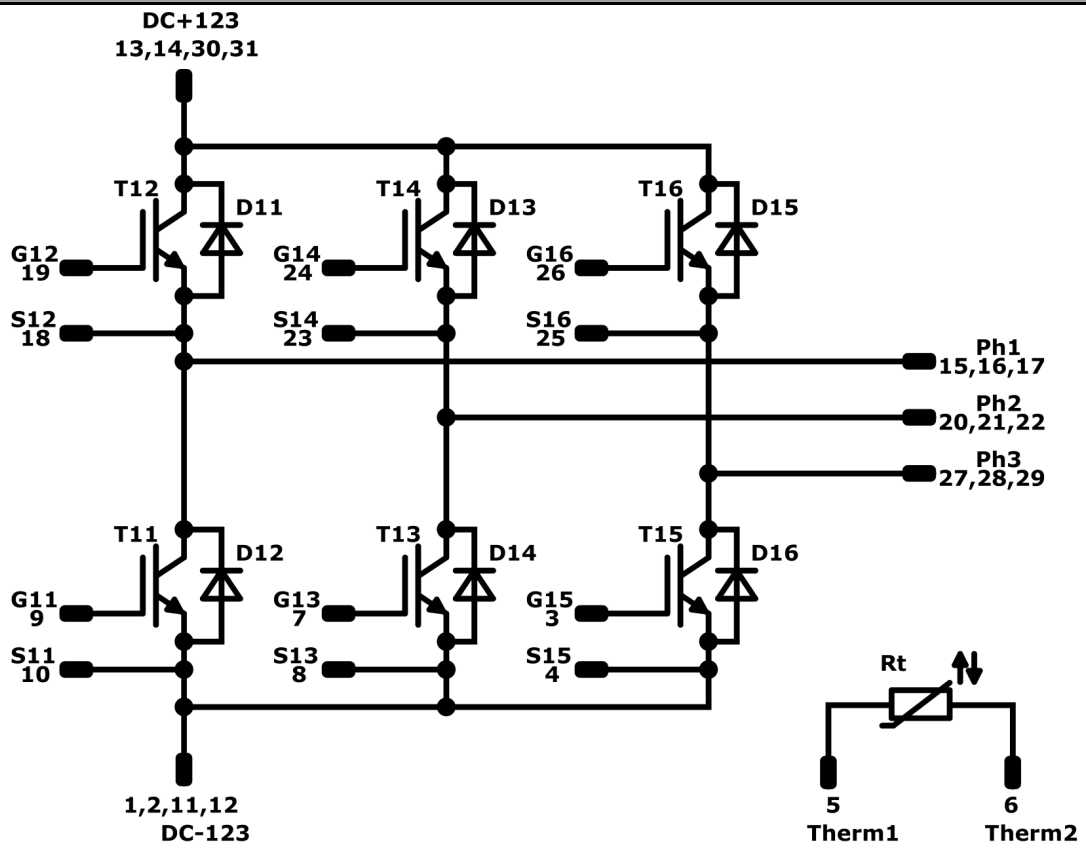
	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Type&Ver	**Lot number**	**Serial**	**Date code**		
Datamatrix	TTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin table			
Pin	X	Y	Functions
1	52,6	0	DC-123
2	49,9	0	DC-123
3	42,65	0	G15
4	39,65	0	S15
5	35,15	0	Therm1
6	28,4	0	Therm2
7	24	0	G13
8	21	0	S13
9	12,2	0	G11
10	9,2	0	S11
11	2,7	0	DC-123
12	0	0	DC-123
13	0	14,65	DC+123
14	2,7	14,65	DC+123
15	0	28,6	Ph1
16	2,7	28,6	Ph1
17	5,4	28,6	Ph1
18	9,6	28,6	S12
19	12,6	28,6	G12
20	19,6	28,6	Ph2
21	22,3	28,6	Ph2
22	25	28,6	Ph2
23	29,7	28,6	S14
24	32,7	28,6	G14
25	39,7	28,6	S16
26	42,7	28,6	G16
27	47,2	28,6	Ph3
28	49,9	28,6	Ph3
29	52,6	28,6	Ph3
30	52,6	14,65	DC+123
31	49,9	14,65	DC+123



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	1200 V	50 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	50 A	Inverter Diode	
Rt	NTC			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 1 packages see vincotech.com website.

Package data
Package data for *flow* 1 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-x1126PA050M7-L828F09x-D1-14	07 Dec. 2017		